

## 20V P-Channel Enhancement Mode MOSFET

### Description

The NP2301AVR uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

### General Features

- ◆  $V_{DS} = -20V$ ,  $I_D = -2.8A$   
 $R_{DS(ON)}(Typ.) = 64m\Omega @V_{GS} = -4.5V$   
 $R_{DS(ON)}(Typ.) = 79m\Omega @V_{GS} = -2.5V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

### Application

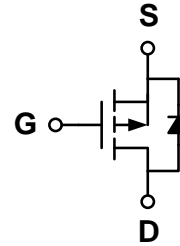
- ◆ PWM applications
- ◆ Load switch

### Package

- ◆ SOT-23

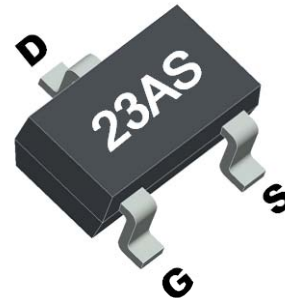


### Schematic diagram



### Marking and pin assignment

SOT-23  
(Topview)



### Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
NP2301AVR-G	-55°C to +150°C	SOT-23	3000

### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	$V_{DS}$	-20	V
Gate-source voltage	$V_{GS}$	±12	V
Drain current-continuous <sup>a</sup> @T <sub>j</sub> =125°C -pulse <sup>b</sup>	$I_D$	-2.8	A
	$I_{DM}$	-11	A
Drain-source Diode forward current	$I_S$	-1.25	A
Maximum power dissipation	$P_D$	1	W
Operating junction Temperature range	$T_j$	-55—150	°C

**Electrical Characteristics** (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF Characteristics</b>						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate-body leakage	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	$\pm 100$	nA
<b>ON Characteristics</b>						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.65	-1.2	V
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-2.8A$	-	64	90	m $\Omega$
		$V_{GS}=-2.5V, I_D=-2.8A$	-	79	120	
Forward transconductance	gfs	$V_{GS}=-5V, I_D=-5A$	-	5	-	S
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{ISS}$	$V_{DS}=-10V, V_{GS}=0V$ $f=1.0MHz$	-	561	-	pF
Output capacitance	$C_{OSS}$		-	61	-	
Reverse transfer capacitance	$C_{RSS}$		-	52	-	
<b>Switching Characteristics</b>						
Turn-on delay time	$t_{D(on)}$	$V_{DD}=-10V$ $I_D=-2.8A$ $V_{GEN}=-4.5V$ $R_L=10ohm$ $R_{GEN}=-60ohm$	-	12.5	-	ns
Rise time	$t_r$		-	6.6	-	
Turn-off delay time	$t_{D(off)}$		-	113	-	
Fall time	$t_f$		-	46.6	-	
Total gate charge	Qg	$V_{DS}=-10V, I_D=-3A$ $V_{GS}=-4.5V$	-	6.1	-	nC
Gate-source charge	Qgs		-	1.7	-	
Gate-drain charge	Qgd		-	1.2	-	
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Diode forward voltage	$V_{SD}$	$V_{GS}=0V, I_S=-1.25A$	-	-0.81	-1.2	V

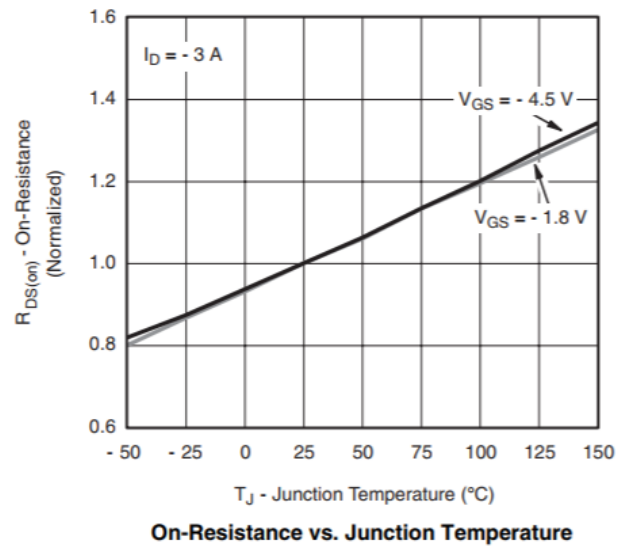
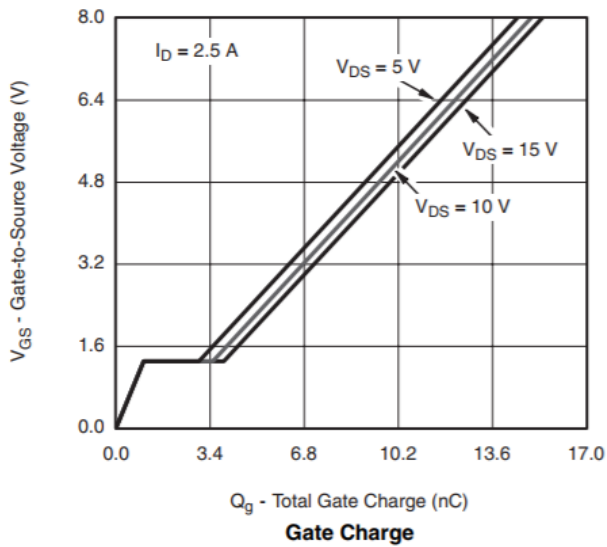
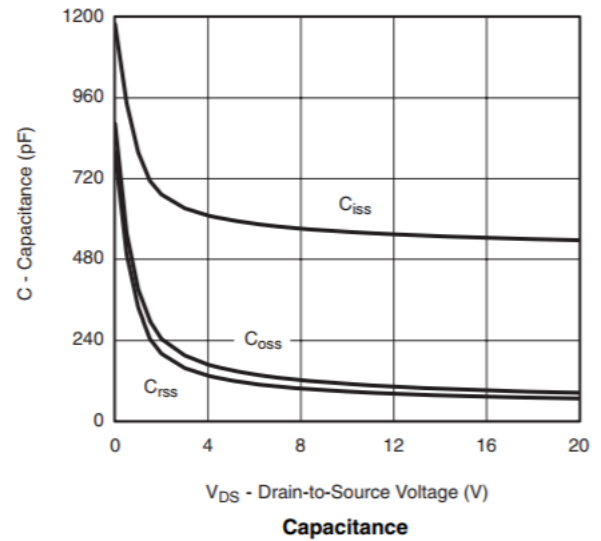
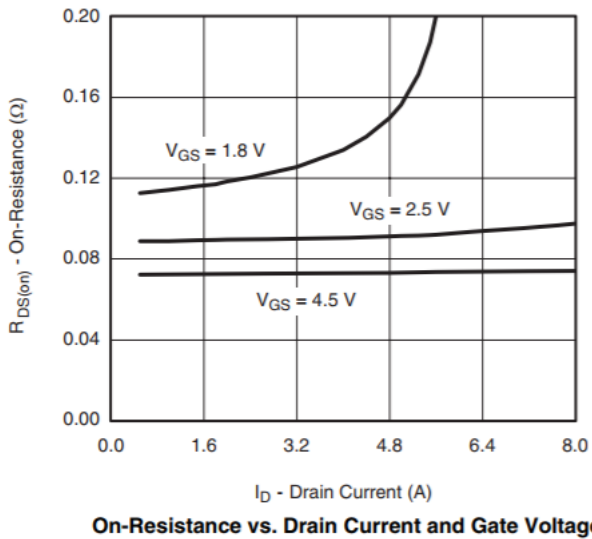
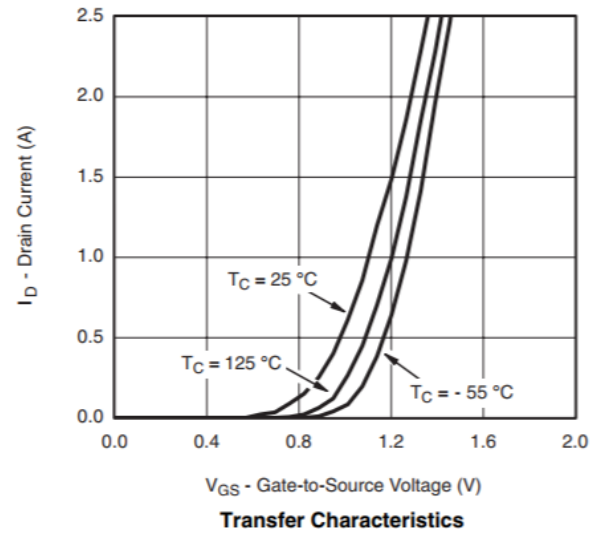
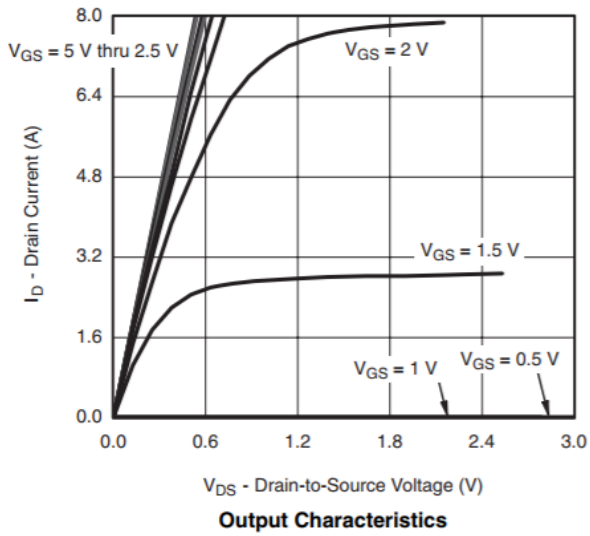
**Notes:**

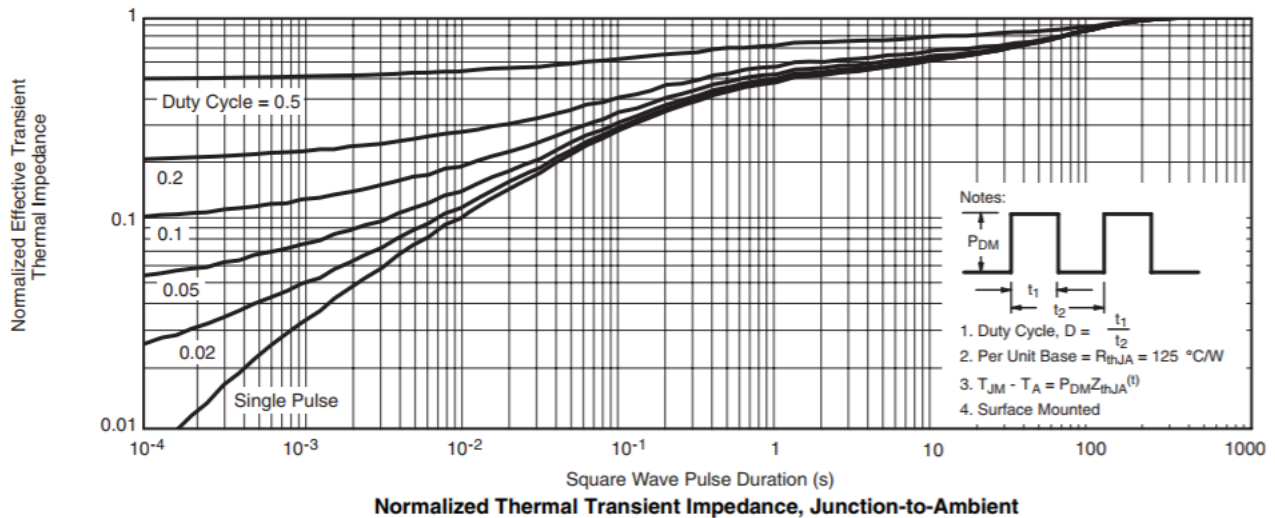
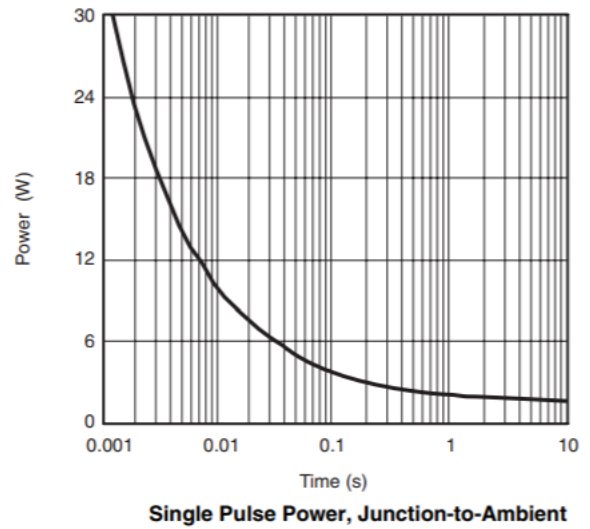
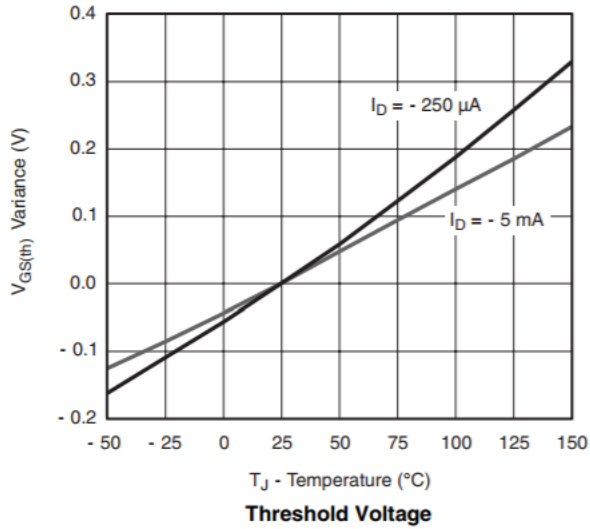
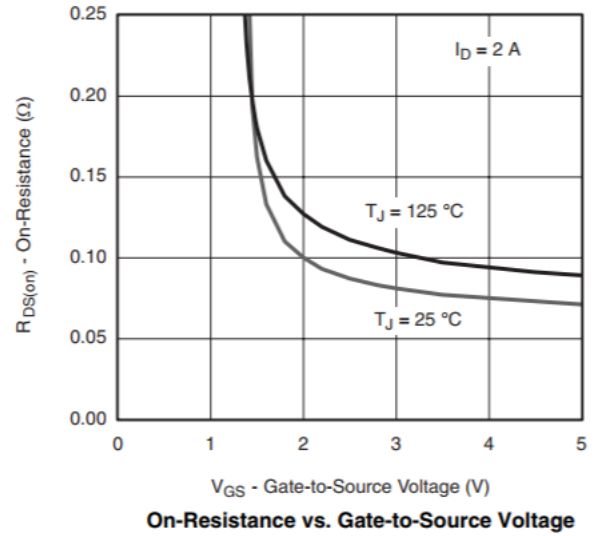
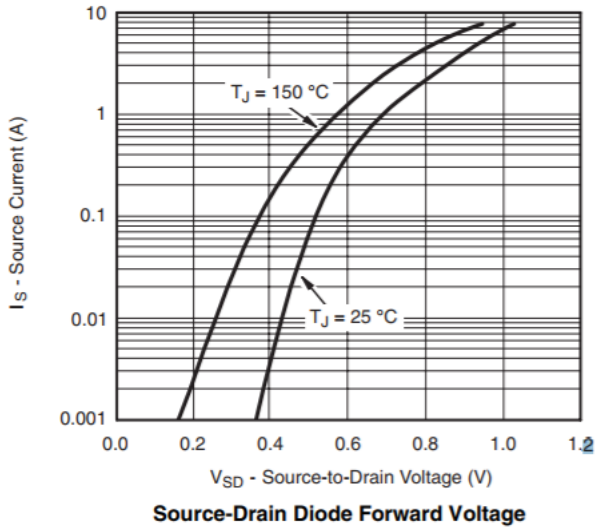
- surface mounted on FR4 board,  $t \leq 10sec$
- pulse test: pulse width  $\leq 300\mu s$ , duty  $\leq 2\%$
- guaranteed by design, not subject to production testing

**Thermal Characteristics**

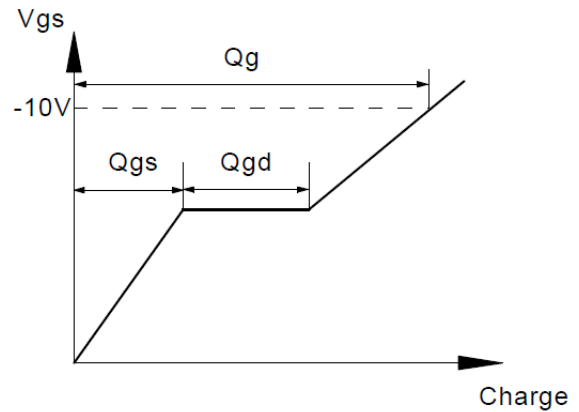
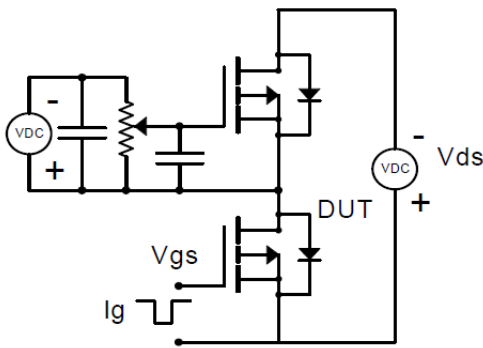
Thermal Resistance junction-to ambient	Rth JA	100	$^{\circ}C/W$
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## Typical Performance Characteristics

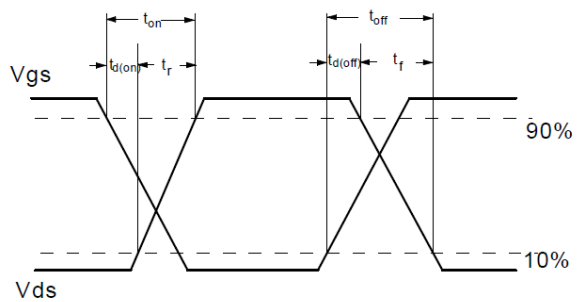
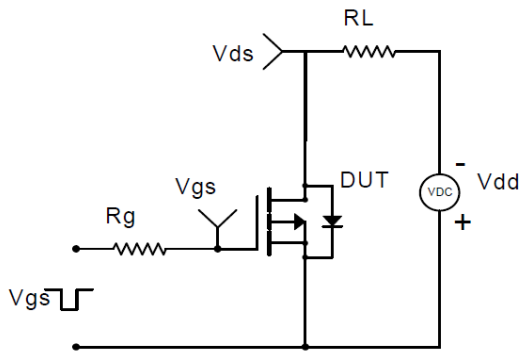




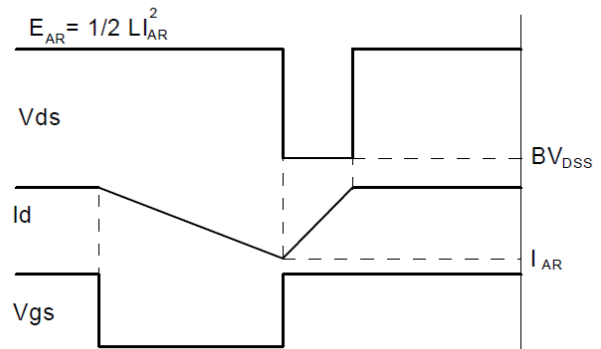
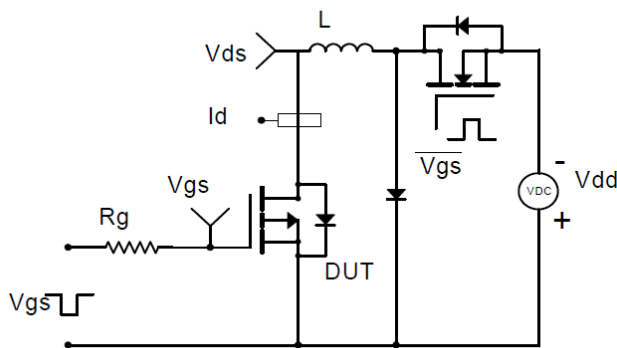
Gate Charge Test Circuit & Waveform



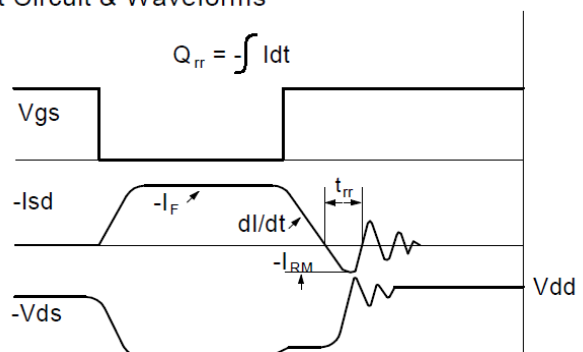
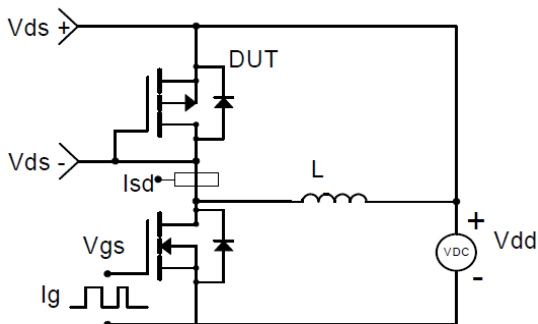
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

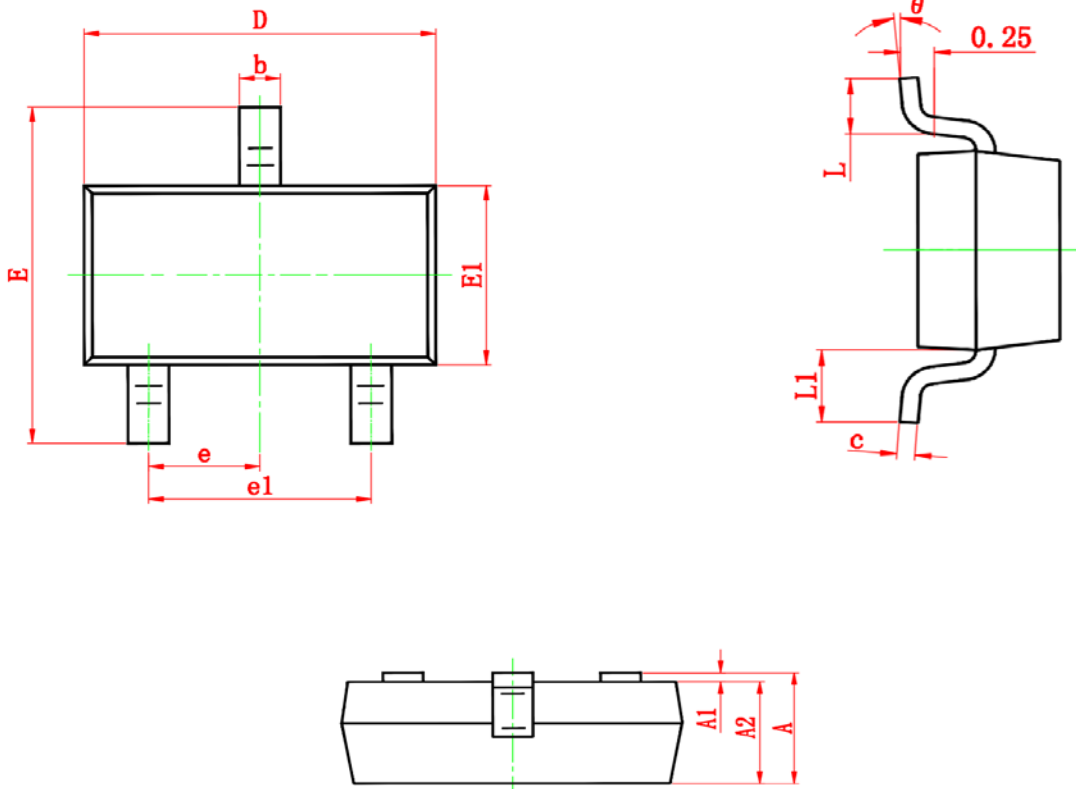


Diode Recovery Test Circuit & Waveforms



## Package Information

- SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	2.250	2.550	0.089	0.100
E1	1.200	1.400	0.047	0.055
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.300	0.500	0.012	0.020
L1	0.550 REF.		0.022 REF.	
θ	0°	8°	0°	8°